

**CPH5805****DC / DC Converter Applications****Features**

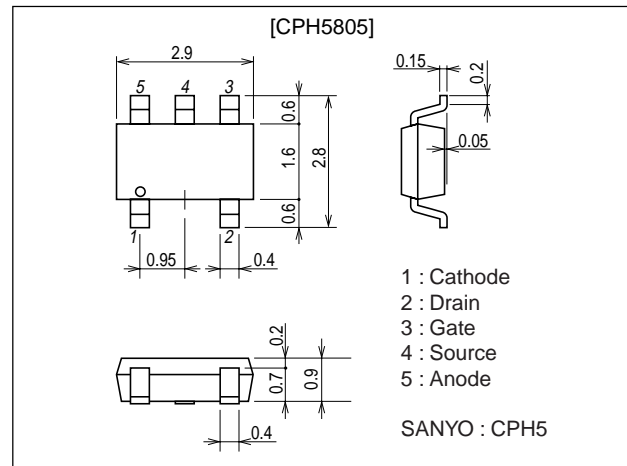
- Composite type with an N-Channel Silicon MOSFET (MCH3412) and a Schottky Barrier Diode (SBS006) contained in one package facilitating high-density mounting.

[MOSFET]

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

[SBD]

- Short reverse recovery time.
- Low forward voltage.

Package Dimensionsunit : mm
2171**Specifications****Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		3	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	12	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (600mm ² X0.8mm) 1unit	0.9	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V _R RM		30	V
Nonrepetitive Peak Reverse Surge Voltage	V _R SM		30	V
Average Output Current	I _O		0.5	A
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	10	A
Junction Temperature	T _J		-55 to +125	°C
Storage Temperature	T _{stg}		-55 to +125	°C

Marking : QF

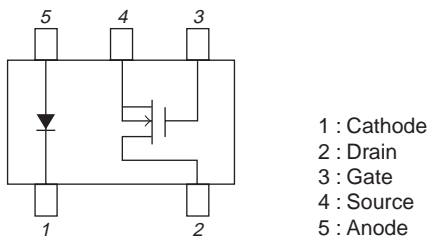
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CPH5805

Electrical Characteristics at Ta=25°C

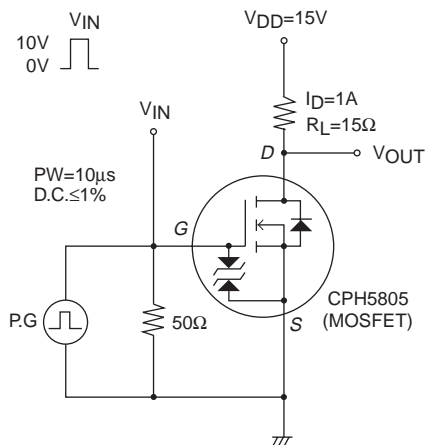
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0$	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	1.2		2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=1.5A$	2.1	3		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=1.5A, V_{GS}=10V$		64	84	$m\Omega$
	$R_{DS(on)2}$	$I_D=1A, V_{GS}=4V$		105	150	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10V, f=1MHz$		180		pF
Output Capacitance	C_{oss}	$V_{DS}=10V, f=1MHz$		42		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, f=1MHz$		25		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		7		ns
Rise Time	t_r	See specified Test Circuit		28		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit		18.5		ns
Fall Time	t_f	See specified Test Circuit		4.4		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=10V, I_D=3A$		4.9		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10V, V_{GS}=10V, I_D=3A$		0.93		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=10V, V_{GS}=10V, I_D=3A$		0.63		nC
Diode Forward Voltage	V_{SD}	$I_S=3A, V_{GS}=0$		0.85	1.2	V
[SBD]						
Reverse Voltage	V_R	$I_R=0.5mA$	30			V
Forward Voltage	V_{F1}	$I_F=0.3A$		0.35	0.4	V
	V_{F2}	$I_F=0.5A$		0.42	0.47	V
Reverse Current	I_R	$V_R=10V$			200	μA
Interterminal Capacitance	C	$V_R=10V, f=1MHz$ cycle		20		pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=100mA$			10	ns

Electrical Connection (Top view)



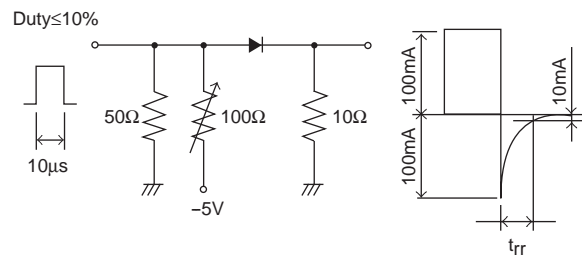
Switching Time Test Circuit

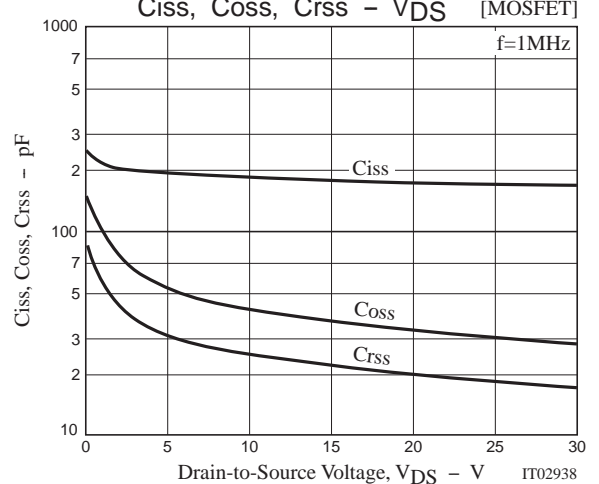
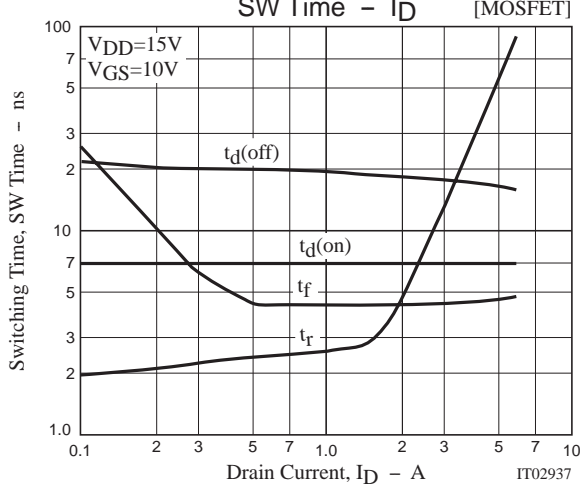
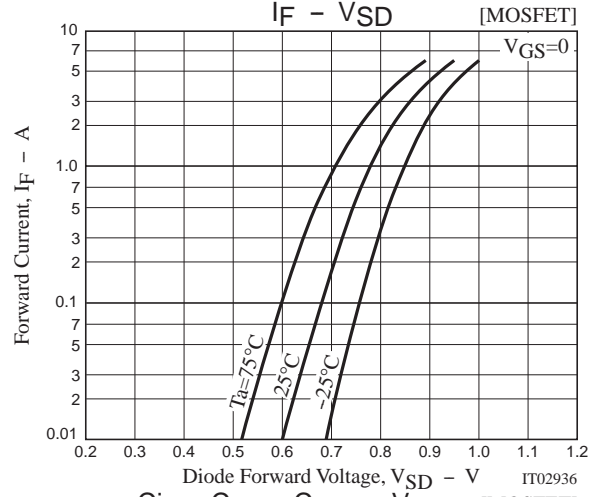
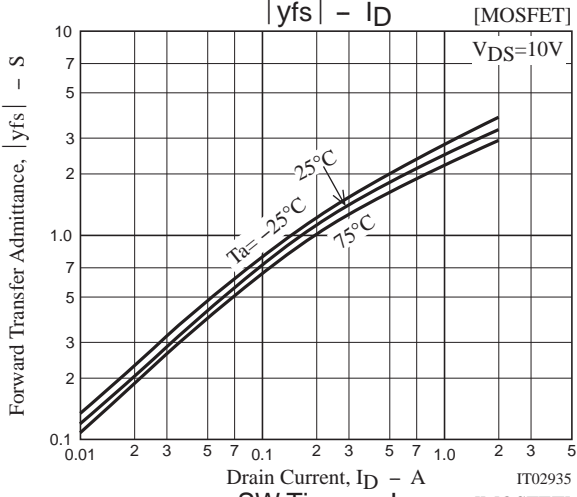
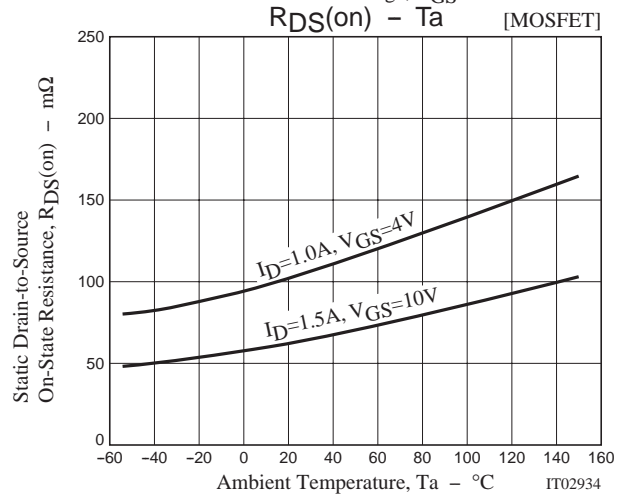
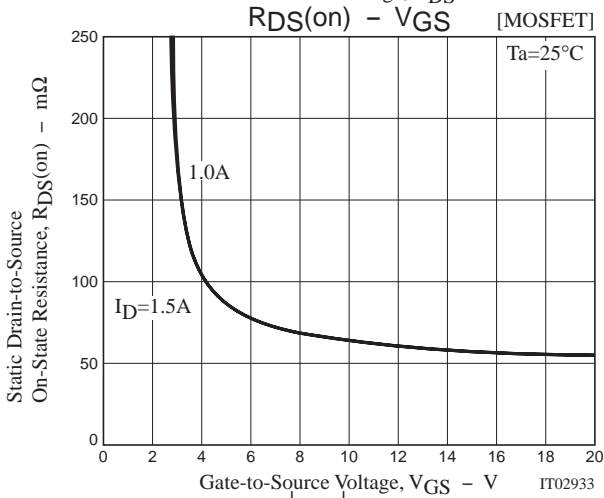
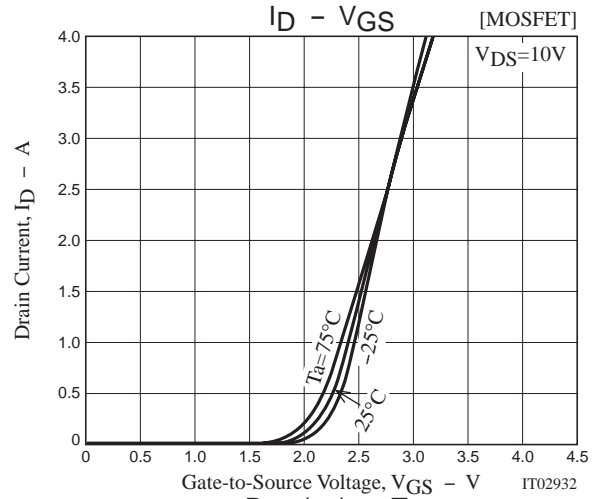
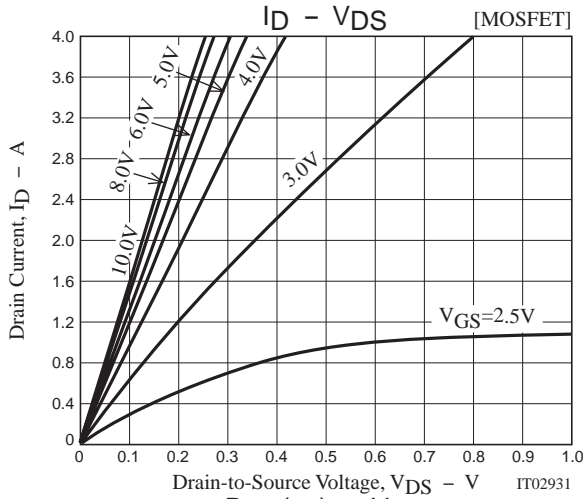
[MOSFET]

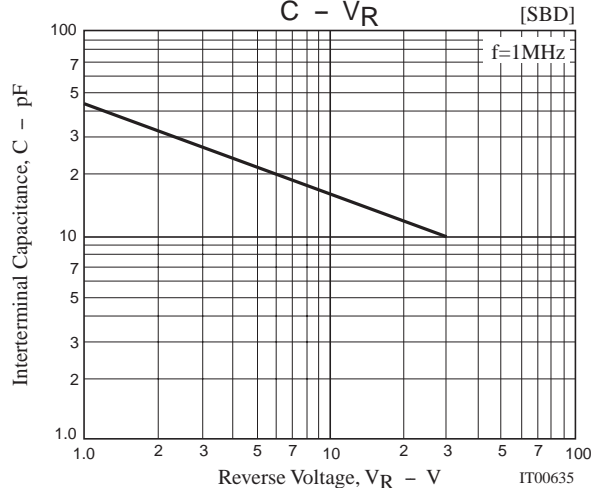
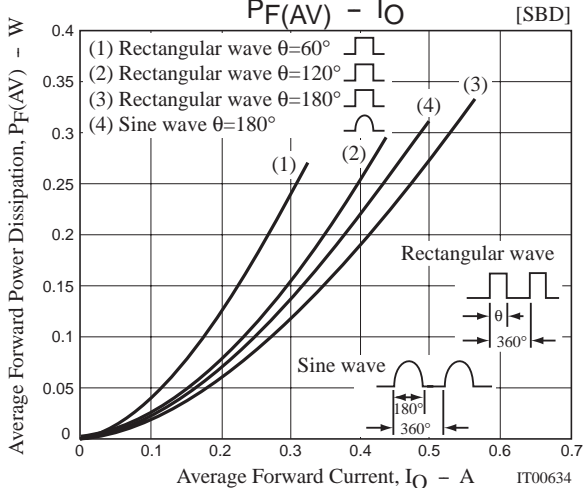
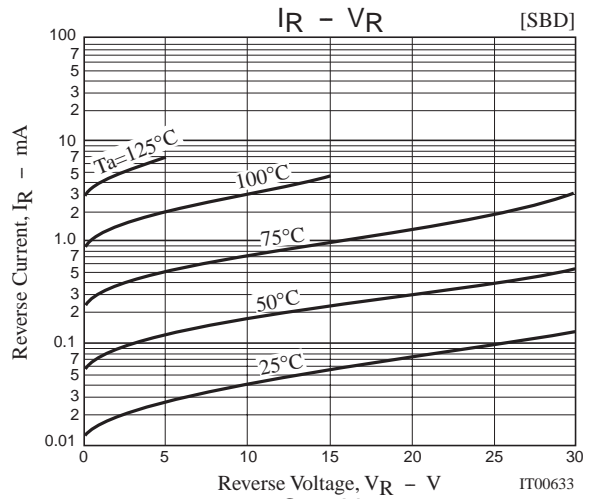
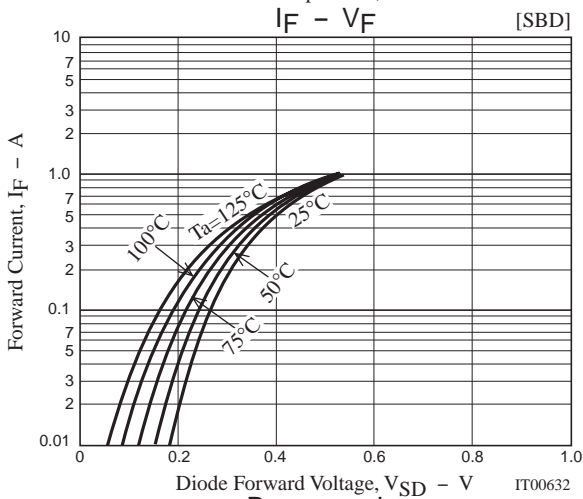
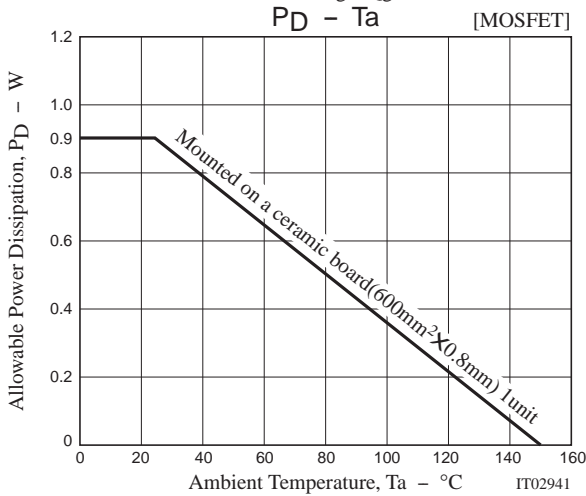
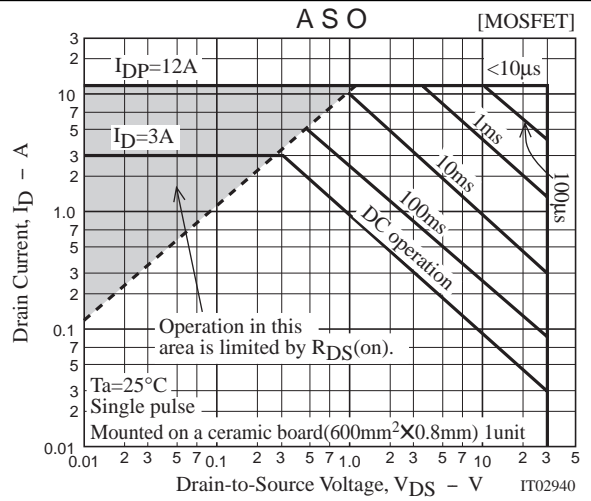
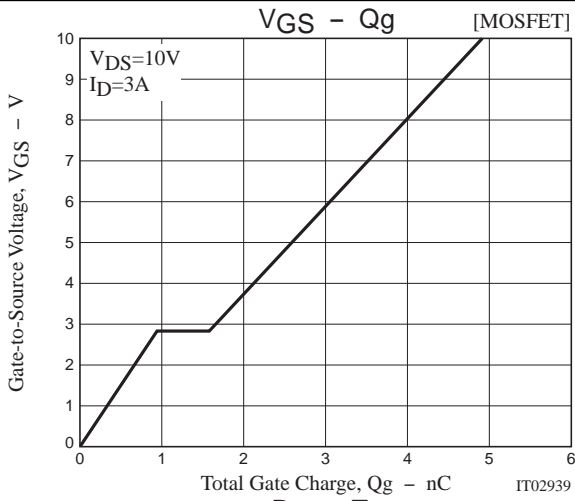


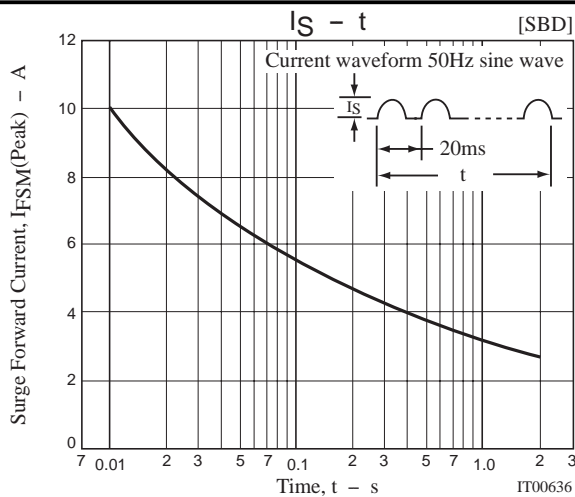
t_{rr} Test Circuit

[SBD]









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